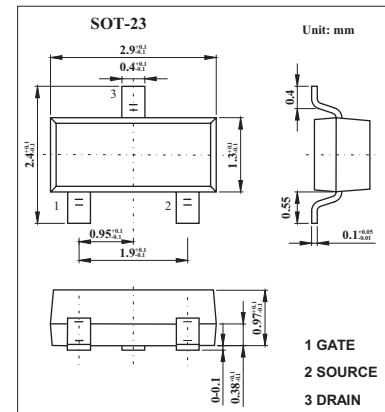


MOS Field Effect Transistor

2SK1828

■ Features

- 2.5V Gate Drive
- Low Threshold Voltage : $V_{th}=0.5$ to $1.5V$
- High Speed



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DS}	20	V
Gate to source voltage	V_{GS}	10	V
Drain current	I_D	50	mA
Power dissipation	P_D	200	mW
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

* $PW \leq 10ms$, duty cycle $\leq 5\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain source breakdown voltage	V_{DS}	$I_D=100 \mu A, V_{GS}=0$	20			V
Drain cut-off current	I_{DSS}	$V_{DS}=20V, V_{GS}=0$			1.0	μA
Gate leakage current	I_{GSS}	$V_{GS}=10V, V_{DS}=0$			1	μA
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=3.0V, I_D=10mA$	20			ms
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=2.5V, I_D=10mA$		25	40	Ω
Input capacitance	C_{iss}	$V_{DS}=3.0V, V_{GS}=0, f=1MHz$		5.5		pF
Output capacitance	C_{oss}			1.6		pF
Reverse transfer capacitance	C_{rss}			6.5		pF
Switching time turn on time	t_{on}	$I_D=10mA, V_{GS(on)}=0$ to $2.5V, V_{DD}=3.0V$		0.14		μs
Switching time turn off time	t_{off}			0.14		μs

■ Marking

Marking	KI
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